Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Extended temperature range T_i = 175 °C
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Tin-plated 100% solderable side pads for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 1.5 kV HBM
- Trench MOSFET technology
- AEC-Q101 qualified

3. Applications

- · Relay driver
- · High-speed line driver
- · Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V _{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	-	3.8	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 3.8 A; T_j = 25 °C		-	55	72	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	157	D
2	D	drain	7	
3	G	gate	2 5	G ←
4	S	source	3 8 4	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	S
7	D	drain		017aaa255
8	S	source		

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMPB55XNEA	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220		

7. Marking

Table 4. Marking codes

Type number	Marking code
PMPB55XNEA	3Q

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V_{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	3.8	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	2.4	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	16	Α
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = 0.3 A; DUT in avalanche (unclamped)		-	6.2	mJ
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	550	mW
			[1]	-	1.95	W
		T _{sp} = 25 °C		-	10	W
Tj	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source-drain d	iode					,
I _S	source current	T _{amb} = 25 °C	[1]	-	1.9	Α
ESD maximum	rating					
V_{ESD}	electrostatic discharge voltage	НВМ	[3]	-	1500	V

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper; tin-plated and standard footprint.

^[3] Measures between all pins.

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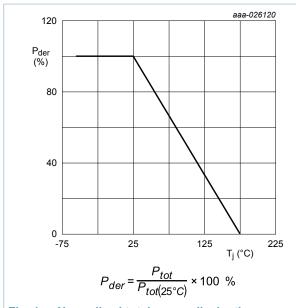


Fig. 1. Normalized total power dissipation as a function of junction temperature

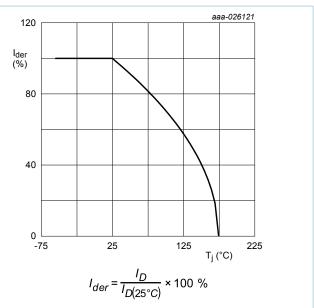


Fig. 2. Normalized continuous drain current as a function of junction temperature

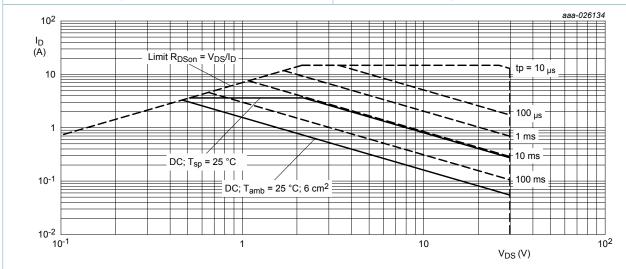


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		[1]	-	236	272	K/W
			[2]	-	67	77	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	12	15	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

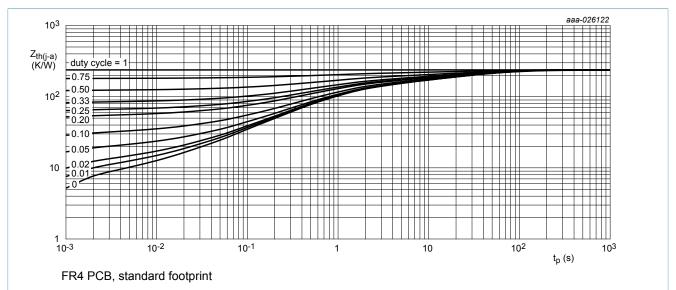


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

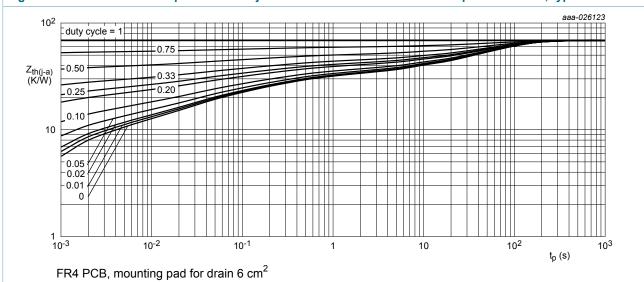


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.75	1	1.25	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μΑ
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μΑ
R _{DSon}	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 3.8 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	55	72	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 3.8 \text{ A}; T_j = 175 \text{ °C}$	-	102	133	mΩ
		$V_{GS} = 2.5 \text{ V}; I_D = 3.1 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	77	110	mΩ
g _{fs}	forward transconductance	V_{DS} = 10 V; I_D = 3.8 A; T_j = 25 °C	-	20	-	S
R_G	gate resistance	f = 1 MHz	-	10.8	-	Ω
Dynamic ch	naracteristics			•		
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 3.6 A; V _{GS} = 4.5 V;	-	3	5	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.5	-	nC
Q_{GD}	gate-drain charge		-	0.9	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	255	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	31	-	pF
C _{rss}	reverse transfer capacitance		-	23	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; I_{D} = 3.6 A; V_{GS} = 4.5 V;	-	7	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	20	-	ns
t _{d(off)}	turn-off delay time		-	18	-	ns
t _f	fall time		-	8	-	ns
Source-dra	in diode					
V_{SD}	source-drain voltage	I _S = 1.9 A; V _{GS} = 0 V; T _j = 25 °C	-	8.0	1.2	V
t _{rr}	reverse recovery time	I _S = 2.5 A; dI _S /dt = -100 A/μs;	-	12.6	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 10 \text{ V}; T_j = 25 \text{ °C}$	-	4	-	nC

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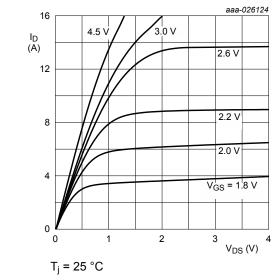


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

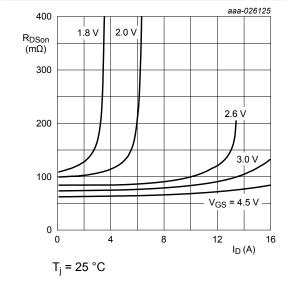


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

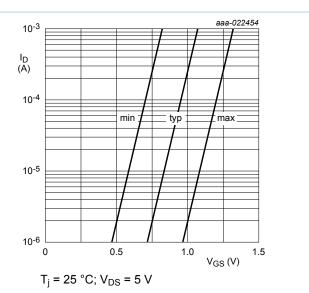


Fig. 7. Subthreshold drain current as a function of gate-source voltage

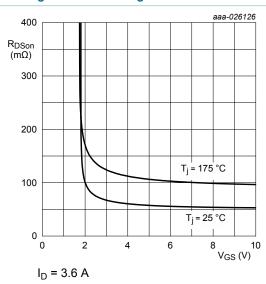


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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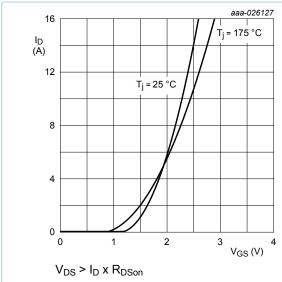


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

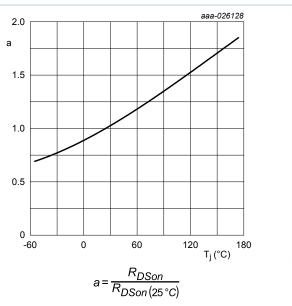


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

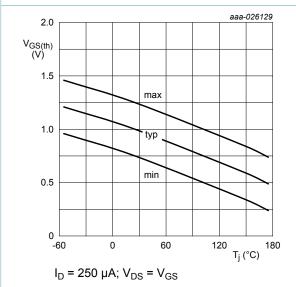


Fig. 12. Gate-source threshold voltage as a function of junction temperature

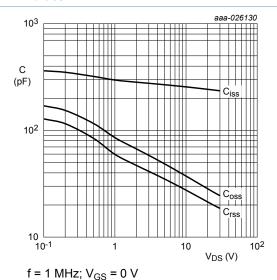
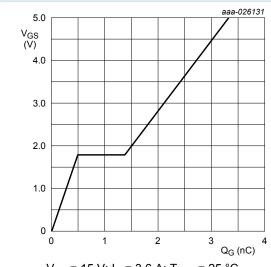


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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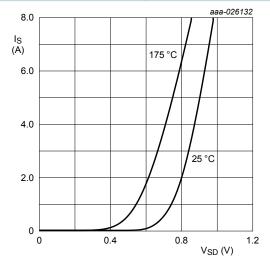


 V_{DS} = 15 V; I_{D} = 3.6 A; T_{amb} = 25 °C

V_{GS}(pl)
V_{GS(th)}
V_{GS(th)}
Q_{GS1}
Q_{GS2}
Q_{GG(tot)}
Q_{GG2}
Q_{G(tot)}
Q_{G3aaa508}

Fig. 15. Gate charge waveform definitions



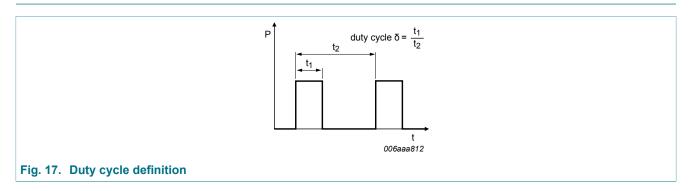


 $V_{GS} = 0 V$

Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information

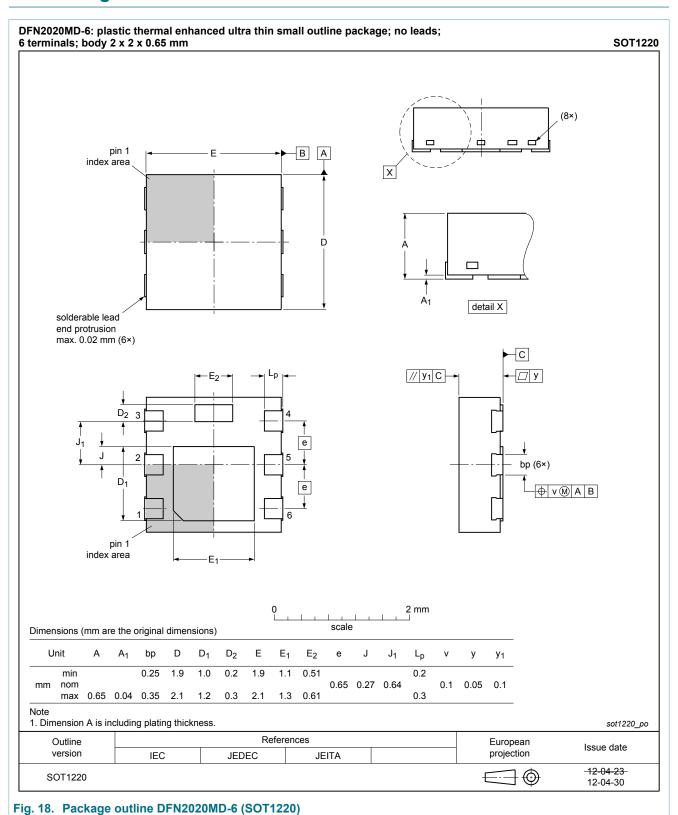


Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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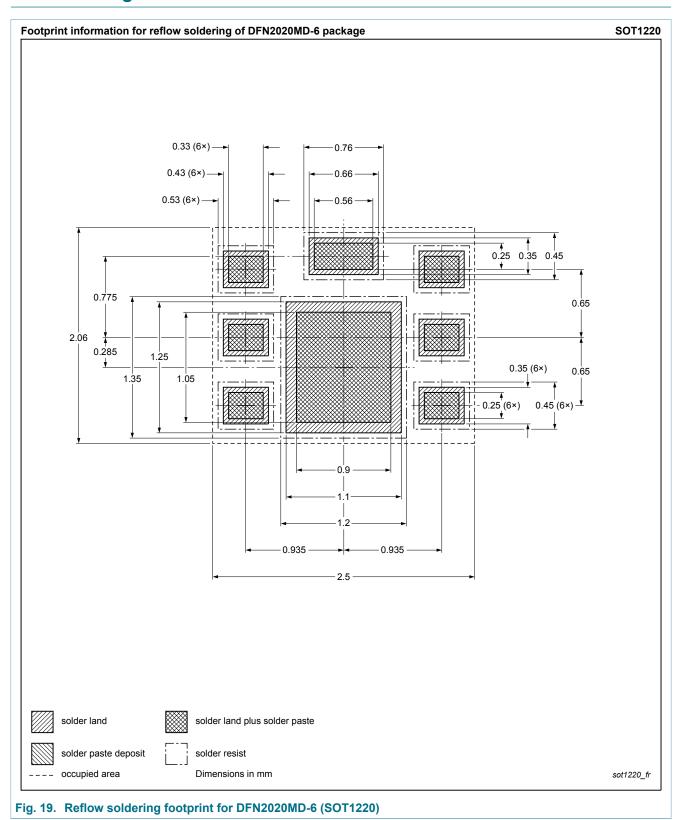
12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Tubio di Novioloni motory								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PMPB55XNEA v.2	20170329	Product data sheet	-	PMPB55XNEA v.1				
Modifications>	Marking code correct	Marking code corrected						
PMPB55XNEA v.1	20170222	Product data sheet	-	-				

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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